# The RF Line NPN Silicon RF Power Transistor

Designed for power amplifier applications in industrial, commercial and amateur radio equipment to 30 MHz.

Specified 12.5 Volt, 30 MHz Characteristics —
 Output Power = 80 Watts
 Minimum Gain = 12 dB
 Efficiency = 50%

## **MAXIMUM RATINGS**

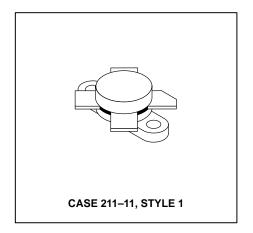
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub> 25		Vdc
Collector-Base Voltage	V <sub>CBO</sub>	45	Vdc
Emitter–Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current — Continuous	IC	20	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	250 1.43	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	°C/W

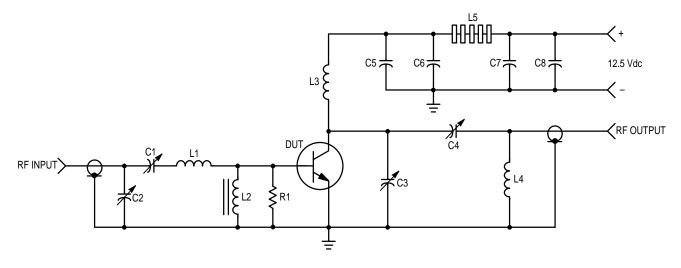
# **MRF454**

80 W, 30 MHz RF POWER TRANSISTOR NPN SILICON



# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	18	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 50 mAdc, V <sub>BE</sub> = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	4.0	_	_	Vdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	hFE	40	_	150	_
DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>CB</sub> = 15 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	_	250	pF
FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 80 W, f = 30 MHz)	G <sub>pe</sub>	12	_	_	dB
Collector Efficiency (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 80 W, f = 30 MHz)	η	50	_	_	%
Series Equivalent Input Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 80 W, f = 30 MHz)	Z <sub>in</sub>	_	.938–j.341	_	Ohms
Series Equivalent Output Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 80 W, f = 30 MHz)	Z <sub>out</sub>	_	1.16–j.201	_	Ohms
Parallel Equivalent Input Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 80 W, f = 30 MHz)	_	_	1.06 Ω 1817 pF	_	_
Parallel Equivalent Output Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 80 W, f = 30 MHz)	_	_	1.19 Ω 777 pF	_	_



C1, C2, C4 — ARCO 469

C3 — ARCO 466

C5 — 1000 pF, UNELCO

C6, C7 — 0.1  $\mu F$  Disc Ceramic

C8 — 1000 μF/15 V Electrolytic

R1 — 10 Ohm/1.0 Watt, Carbon

L1 - 3 Turns, #18 AWG, 5/16" I.D., 5/16" Long

L2 — VK200–20/4B, FERROXCUBE

L3 — 12 Turns, #18 AWG Enameled Wire, 1/4" I.D., Close Wound

L4 - 3 Turns 1/8" O.D. Copper Tubing, 3/8" I.D., 3/4" Long

L5 — 7 FERRITE Beads, FERROXCUBE #56-590-65/3B

Figure 1. 30 MHz Test Circuit Schematic

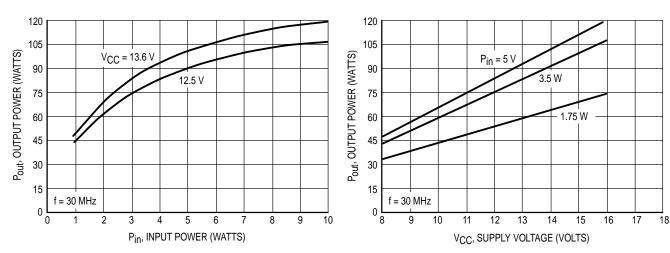
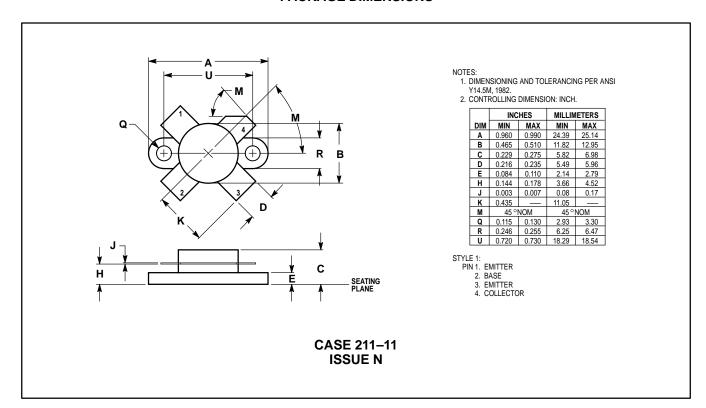


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Supply Voltage

## **PACKAGE DIMENSIONS**



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